A PVT-Insensitive Body-Biased Time-to-Digital Converter in 28nm FD-SOI CMOS Technology

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Outline

Introduction – dToF sensor and FD-SOI

• Architecture of the TDC pixels and the DLL

• Experimental results

Conclusion

Direct Time-of-Flight (dToF) Systems



... in Different Depth Scenes



Direct Time-of-Flight (dToF) Systems



Process, Voltage, Temperature (PVT) variation



Conventional PVT-insensitive TDC Design





This Work

- Planar technology
- Lower leakage current
- Lower process variability
- Vertical double gate structure



Fully Depleted Silicon-on-Insulator (FD-SOI)

[STMicroelectronics]



This Work

- Planar technology
- Lower leakage current
- Lower process variability
- Vertical double gate structure
- Efficient Vth modulation
- SPAD integration capability





Chip Proposed



Manufactured in 28nm FD-SOI CMOS



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DLL-based TDC Architecture





DLL-based TDC Architecture





Body-biased Delay Element







TDC Range 0 (0.87ns)



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TDC Range 1 (1.76ns)



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TDC Range 2 (2.24ns)



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DLL-based TDC Architecture











512 tap: 15ns range / 66.66MHz

























[G.de Stree et al. JSSC 2017]



DLL Measurement





Readout token gen SPAD enable buffer

Experimental Setup









Propagation delay time against control voltages



- Open-loop Configuration
- Tunning range: ~15.5ps/bin



DLL Phase Skew vs. Supply

14x smaller variations in closed-loop DLL under 10% VDD change



DLL Phase Skew vs. Freq

Phase skew only changes 0.12ns against 2ns STOP period change (20% frequency variation)



Duty cycle Full Sweep

Average duty cycle: 49.52%





TDC Electrical Measurement



The SPAD_IN of the test TDC pixel is driven by an FPGA, allowing for a 15ps delay step.



TDC Bin Size Electrical Measurement



Estimated bin size = COM difference/delay difference

		VDD		
IDC Range		0.97V	1V	1.03V
Closed-loop estimated bin size (ps)	Short	52.46	54.61	51.418
	Middle	110.02	110.13	110.15
	Long	140.68	140.58	140.51
Open-loop estimated bin size (ps)	Short	55.20	47.47	41.15
	Middle	110.57	105.90	99.20
	Long	147.99	140.37	127.57

TDC Code Density Test



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TDC Non-linearity



Range 0 (0.87ns)
Range 1 (1.76ns)
Range 2 (2.24ns)

	Range0	Range1	Range2
DNL(LSB)	+0.24/-0.09	+0.21/-0.15	+0.31/-0.11
INL(LSB)	+0.22/-0.26	+0.28/0	+0.31/0

CMOS Sensors & Systems Group

Conclusions

- First body-biased TDC pixel in 28nm FDSOI
- A novel DLL solution for the negative body-biased voltage generation
- Demonstrates the body-biased TDC's robustness against voltage and frequency variations
- Requires optical IRF characterisation with SPAD, variation assessment across the TDC pixel array

Performance Summary Table						
Technology		28nm FDSOI				
Histogram bins	16*11b					
STOP frequency		100MHz				
Pixel size	$12.02 imes 29.87 \mu m^2$					
TDC resolution/ps	54.6	110.1	140.5			
TDC range / ns	0.87	1.76	2.24			
TDC DNL / LSB	+0.24/-0.09	0.21/-0.15	+0.31/-0.11			
TDC INL / LSB	+0.22/-0.26	+0.28/0	+0.31/0			

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Thank you

